

■ Features

- Epitaxial planar die construction
- Complementary to PZT2907A


SOT-223

1. BASE
2. COLLECTOR
3. EMITTER

■ Absolute Maximum Ratings Ta = 25°C

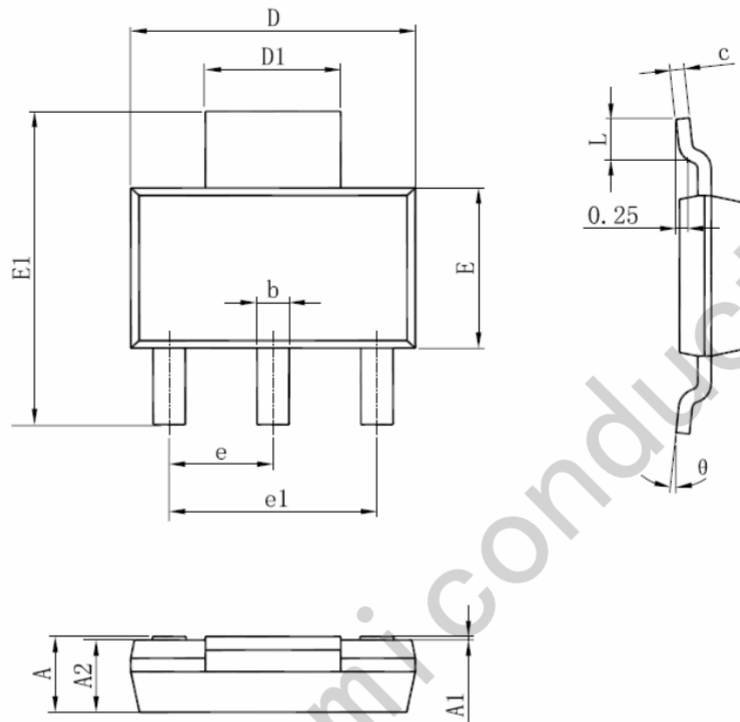
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	75	V
Collector - Emitter Voltage	V _{CEO}	40	
Emitter - Base Voltage	V _{EBO}	6	
Collector Current - Continuous	I _C	600	mA
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E = 0	75			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B = 0	40			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100 μA, I _C = 0	6			
Collector-base cut-off current	I _{CB0}	V _{CB} = 75 V, I _E = 0			100	nA
Collector cut-off current	I _{CEX}	V _{CE} = 60 V, V _{EB(off)} =-3V			100	
Emitter cut-off current	I _{EBO}	V _{EB} = 6V, I _C =0			100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =150 mA, I _B =15mA			0.3	V
		I _C = 500 mA, I _B = 50mA			1	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =150 mA, I _B =15mA			1.2	
		I _C = 500 mA, I _B = 50mA			2	
DC current gain	h _{FE(1)}	V _{CE} = 10V, I _C = 0.1mA	35			
	h _{FE(2)}	V _{CE} = 10V, I _C = 1mA	50			
	h _{FE(3)}	V _{CE} = 10V, I _C = 10mA	75			
	h _{FE(4)}	V _{CE} = 10V, I _C = 150mA	100		300	
	h _{FE(5)}	V _{CE} = 1V, I _C = 150mA	50			
	h _{FE(6)}	V _{CE} = 10V, I _C = 500mA	40			
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V			10	nS
Rise time	t _r	I _C =150mA, I _{B1} =15mA			25	
Storage time	t _s	V _{CC} =30V, I _C =150mA, I _{B1} =-I _{B2} =15mA			225	
Fall time	t _f		60			
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz			8	
Transition frequency	f _T	V _{CE} = 20V, I _C = 20mA, f=100MHz	300			MHz

Package Information

SOT-223



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°

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